

Low temperature sintering of BaO–Sm₂O₃–4TiO₂ ceramics

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Abstract

The effect of B₂O₃ and CuO on the sintering temperature and microwave dielectric properties of BaSm₂Ti₄O₁₂ ceramics was investigated. The BaSm₂Ti₄O₁₂ ceramics were able to be sintered at 1000 °C when B₂O₃ was added. This decrease in the sintering temperature of the BaSm₂Ti₄O₁₂ ceramics upon the addition of B₂O₃ is attributed to the BaB₄O₇ second phase, whose melting temperature is around 900 °C. The B₂O₃ added BaSm₂Ti₄O₁₂ ceramics alone were not able to be sintered below 1000 °C, but were sintered at 875 °C when CuO was added. BaCu(B₂O₅) second phase might be responsible for the decrease in the sintering temperature of the CuO and B₂O₃ added BaSm₂Ti₄O₁₂ ceramics. The BaSm₂Ti₄O₁₂ + 10.0 mol% B₂O₃ + 20.0 mol% CuO ceramics sintered at 875 °C for 2 h have good microwave dielectric properties of $\epsilon_r = 61.47$, $Q \times f = 4256$ GHz and $\tau_f = -9.25$ ppm/°C. The BaCu(B₂O₅) is also a good additive for decreasing the sintering temperature of the BaSm₂Ti₄O₁₂ ceramics.

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1. Introduction

The miniaturization and hybridization of microwave dielectric components are required for the development of mobile telecommunication systems, and various multi-layer devices have been extensively investigated in an attempt to satisfy these requirements. Multi-layer devices consist of alternating microwave dielectric ceramics and internal metallic electrode layers.¹ Ag has been widely used as the metallic electrode, because of its high conductivity and low cost. However, the melting temperature of Ag is low, about 961 °C, whereas the sintering temperature of the microwave dielectric ceramics is generally above 1400 °C. Therefore, for the fabrication of multi-layer devices, it is necessary to develop microwave dielectric ceramics with a low sintering temperature, which can be co-fired with Ag.

BaO–Sm₂O₃–TiO₂ ceramics, consisting of two ternary phases, viz. BaO–Sm₂O₃–5TiO₂ and BaO–Sm₂O₃–3TiO₂, were first reported by Ouchi and co-workers and the crystal

structure of these phases was identified as a tungsten–bronze type structure.^{2–4} In particular, BaSm₂Ti₄O₁₂ ceramics show good microwave dielectric properties of $Q = 2289$ at 3.6 GHz and $\epsilon_r = 78.91$.⁵ However, the sintering temperature of this ceramic is relatively high, being approximately 1350 °C. Therefore, it is necessary to decrease sintering temperature for the application to LTCC technology. In a previous work, B₂O₃/Ge₂O₂ and Bi₂O₃/MnO₂ were used to reduce the sintering temperature of Ba_{6–3x}R_{8+2x}Ti₁₈O₅₄ (where R = Sm, Nd, Pr or La) and [(Pb, Ca)La](Fe, Nb)O₃ ceramics, respectively, however their sintering temperatures were still too high for Ag metal to be used as an electrode.^{6,7} Recently, many types of glasses were used to decrease the sintering temperature of BaNd₂Ti₄O₁₂ ceramics.^{8–10} However, the microwave dielectric properties of the resulting ceramics were not satisfactory, because the addition of glass usually degraded their microwave dielectric properties.

In previous studies, the addition of a small amount of B₂O₃ and CuO was found to reduce the sintering temperature of Ba(Zn_{1/3}Ta_{2/3})O₃, and Ba(Zn_{1/3}Nb_{2/3})O₃ ceramics to below 900 °C.^{11,12} Therefore, it is also possible that these B₂O₃ and CuO additives would be effective in decreasing the sintering temperature of the BaSm₂Ti₄O₁₂ ceramics. In this work, small amounts of B₂O₃ and CuO additives were used to decrease the

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sintering temperature of $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics and the variations in the microwave dielectric properties of these ceramics were investigated in terms of their microstructure.

2. Experimental procedure

BaCO_3 , Sm_2O_3 and TiO_2 (High Purity Chemicals, >99%, Japan) were mixed in a nylon jar with zirconia balls for 24 h, and then dried and calcined at 1100°C for 3 h. After remilling with the B_2O_3 and CuO (High purity Chemicals, >99%) additives, the powder was dried, pressed into discs and sintered at 875 – 1000°C for 2 h. The microstructure of the specimens was studied using X-ray diffraction (Rigaku D/max-RC, Japan), scanning electron microscopy (SEM; Hitachi S-4300, Japan) and transmission electron microscopy (TEM; Hitachi H-9000NAR Ibaraki, Japan). The densities of the sintered specimens were measured by a water-immersion technique. The dielectric properties in the microwave frequency range were measured by a dielectric post resonator technique suggested by Hakki and Coleman¹³ and Courtney.¹⁴ The temperature coefficients of the resonant frequency was measured in the temperature range of 25 – 80°C .

3. Results and discussion

The normal sintering temperature of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics is approximately 1350°C , however they were able to be sintered at 1000°C when B_2O_3 was added. Fig. 1 shows the X-ray diffraction patterns of $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics calcined at 1150°C for 3 h and the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + x\text{B}_2\text{O}_3$ ceramics with $10.0 \leq x \leq 50.0$ mol% sintered at 1000°C for 2 h. All of the peaks were indexed as those of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ phase with lattice parameters of $a = 2.23$ nm, $b = 1.21$ nm and $c = 0.38$ nm. Peaks for the BaB_4O_7 second phase, which are indicated by an asterisk, were also observed for the specimens with $x \geq 10.0$. According to the phase diagram, the eutectic temperature of

the BaB_4O_7 ceramics is approximately 899°C .¹⁵ Therefore, the BaB_4O_7 phase existed as the liquid phase during the sintering process and assisted in the densification of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics. The unknown peaks which are indicated by the open circle were also observed and they might be related to the phase which is formed by the decomposition of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics due to the formation of the BaB_4O_7 phase.

The SEM images of the thermally etched $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + x\text{B}_2\text{O}_3$ ceramics are shown in Fig. 2(a–c). For the specimen with $x = 5.0$ mol%, a porous microstructure with an average grain size of $0.2 \mu\text{m}$ was developed. A dense microstructure formed in the specimen with $x = 10.0$ mol%, but the microstructure was degraded when the amount of B_2O_3 exceeded 10.0 mol% as shown in Fig. 2(c). As the B_2O_3 content increased, the amount of liquid phase increased, and this liquid phase could have evaporated during the sintering process. Therefore, the porous microstructure formed in the specimens with a large amount of B_2O_3 might be due to the evaporation of the liquid phase during sintering.

Fig. 3 shows the variations in the relative density, ϵ_r value and $Q \times f$ value of the B_2O_3 added $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics sintered at 1000°C for 2 h. The relative density of the specimen with 5.0 mol% of B_2O_3 was approximately 85% of the theoretical density and increased with increasing B_2O_3 content, showing a maximum value when $x = 10.0$ mol%. When x exceeded 10.0 mol%, the relative density decreased, and this decrease is attributed to the development of the porous microstructure. The variation in the value of ϵ_r is similar to that of the relative density and, thus, the density is an important factor in improving the value of ϵ_r . The Q -value decreased with increasing B_2O_3 content, even though the relative density increased. This decrease in the Q -value might be due to the increase of the BaB_4O_7 second phase. In addition, the decomposition of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ and the presence of cation deficiency in $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ due to the formation of BaB_4O_7 phase can also deteriorate the $Q \times f$ value of the specimens.

The sintering temperature of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics was reduced to 1000°C when B_2O_3 was added. However, the B_2O_3 added $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics were not able to be sintered below 1000°C and, thus, it is difficult to use Ag as the electrode for B_2O_3 added $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics. To overcome this difficulty, both CuO and B_2O_3 were added to the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics, in order to reduce the sintering temperature below 900°C . When CuO was added to the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramic containing 10.0 mol% B_2O_3 , it was able to be sintered even at 850°C . Fig. 4 shows the X-ray diffraction patterns of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0$ mol% $\text{B}_2\text{O}_3 + x\text{CuO}$ ceramics where $5.0 \leq x \leq 50.0$ mol% sintered at 875°C for 2 h. All of the peaks were identified as those of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ phase. The CuO itself cannot decrease the sintering temperature of $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics below 900°C , because the CuO added $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics were not sintered below 1050°C . Fig. 5 shows the TEM high resolution lattice image of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0$ mol% $\text{B}_2\text{O}_3 + 20.0$ mol% CuO ceramics sintered at 875°C for 2 h. The liquid phase existed at the triple point of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics. According to a previous work, $\text{BaCu}(\text{B}_2\text{O}_5)$ second phase, which melts at a

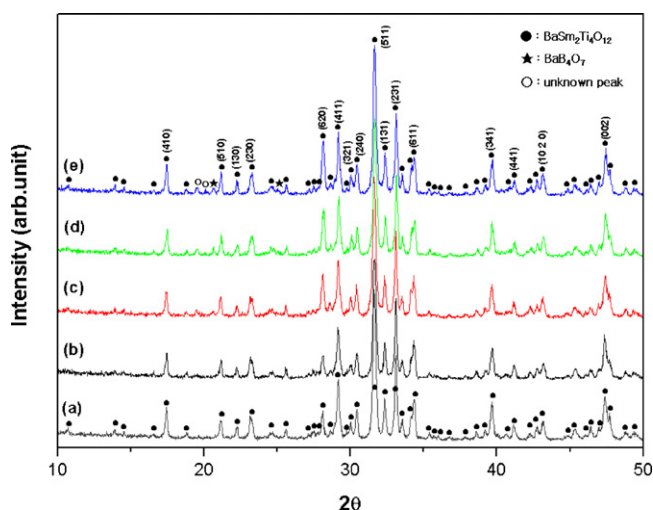


Fig. 1. X-ray diffraction patterns of (a) the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics calcined at 1150°C for 3 h and the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + x\text{B}_2\text{O}_3$ ceramics with $10.0 \leq x \leq 50.0$ mol% sintered at 1000°C for 2 h: (b) $x = 10.0$ mol%, (c) $x = 20.0$ mol%, (d) $x = 30.0$ mol% and (e) $x = 50.0$ mol%.

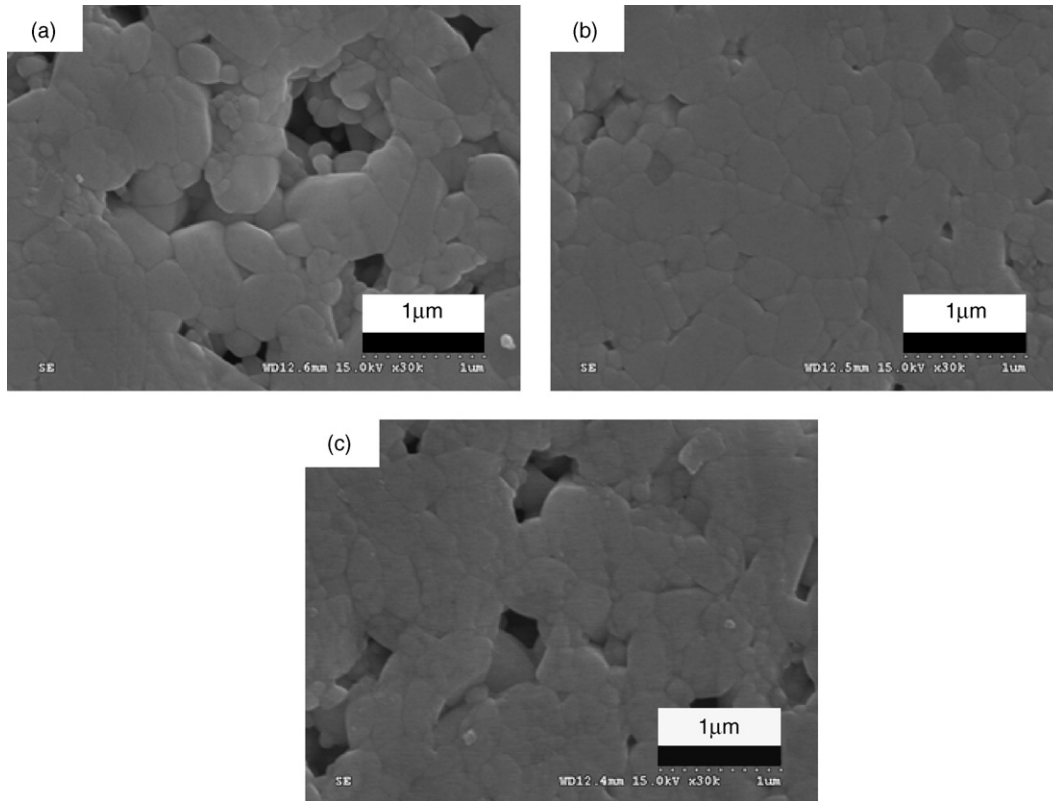


Fig. 2. SEM images of the thermally etched $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + x\text{B}_2\text{O}_3$ ceramics: (a) $x = 5.0$ mol%, (b) $x = 10.0$ mol% and (c) $x = 20.0$ mol%.

temperature above 800°C , existed in the CuO and B_2O_3 added $\text{Ba}(\text{Zn}_{1/3}\text{Nb}_{2/3})\text{O}_3$ ceramics and assisted in the densification at low temperature.¹² For the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics, even if it is difficult to find the peak for $\text{BaCu}(\text{B}_2\text{O}_5)$ in the X-ray diffraction pattern, it is possible that a small amount of the $\text{BaCu}(\text{B}_2\text{O}_5)$ liquid phase formed as shown in Fig. 5 and assisted in the densification of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramic at low temperature. Furthermore, the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics was well sintered even at 875°C when a small amount of the $\text{BaCu}(\text{B}_2\text{O}_5)$ additive was added, as will be discussed later. Therefore, it is considered that the $\text{BaCu}(\text{B}_2\text{O}_5)$ second phase is responsible for the densification of the CuO and B_2O_3 added $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics

at low temperature. In addition, the $\text{CuB}_8\text{O}_{13}$ phase melts at a temperature above 750°C .¹⁶ Therefore, we cannot completely exclude the possibility that the CuO reacted with the B_2O_3 , resulting in the formation of $\text{CuO}-\text{B}_2\text{O}_3$ phase, which assisted in the sintering of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics below 900°C .

Fig. 6(a–c) show the SEM images of the thermally etched surfaces of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0$ mol% $\text{B}_2\text{O}_3 + x\text{CuO}$ ceramics with $5.0 \leq x \leq 20.0$ mol% sintered at 875°C for 2 h. For the

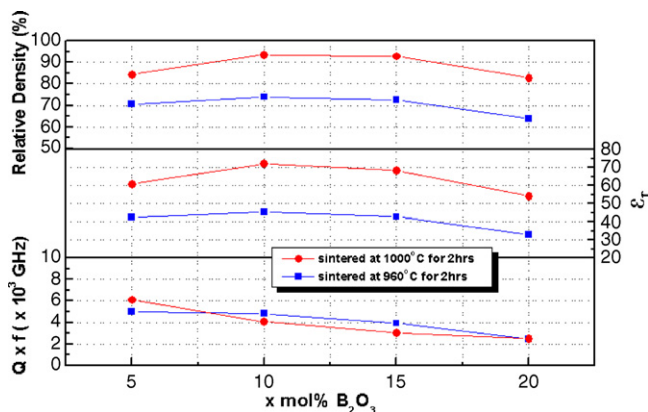


Fig. 3. Variations in the relative density, ϵ_r value and $Q \times f$ value of the B_2O_3 added $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics sintered at 1000°C for 2 h.

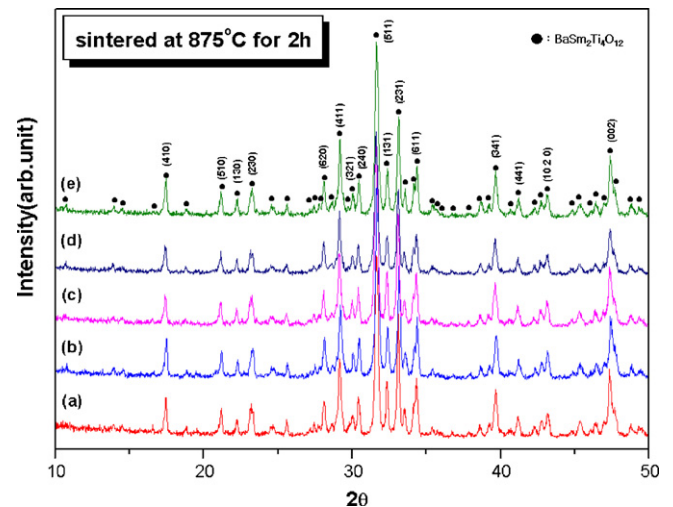


Fig. 4. X-ray diffraction patterns of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0$ mol% $\text{B}_2\text{O}_3 + x\text{CuO}$ ceramics where $5.0 \leq x \leq 50.0$ mol% sintered at 875°C for 2 h: (a) $x = 5.0$ mol%, (b) $x = 10.0$ mol%, (c) $x = 20.0$ mol%, (d) $x = 30.0$ mol% and (e) $x = 50.0$ mol%.

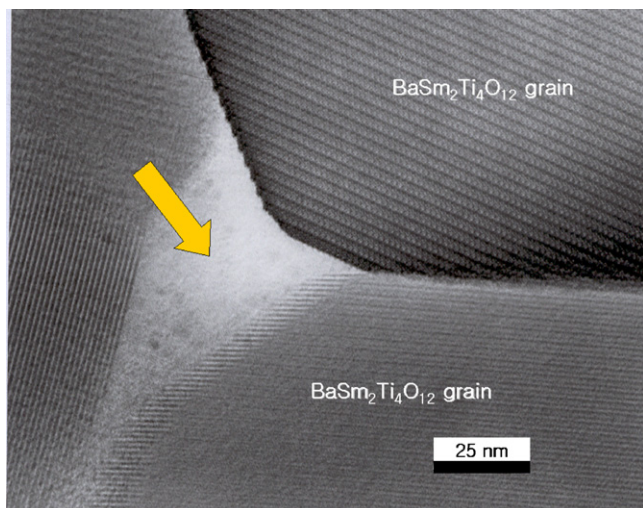


Fig. 5. TEM high resolution lattice image of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0 \text{ mol\% B}_2\text{O}_3 + 20.0 \text{ mol\% CuO}$ ceramics sintered at 875°C for 2 h.

specimen with 5.0 mol% of CuO, a porous microstructure was formed. However, when the CuO content exceeded 10.0 mol%, a dense microstructure developed. Moreover, the microstructure was not degraded when a large amount of CuO was added. Therefore, at least 10.0 mol% of CuO is required to ensure the densification of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0 \text{ mol\% B}_2\text{O}_3$ ceramics.

Fig. 7 shows the variations in the absolute density and ϵ_r value of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0 \text{ mol\% B}_2\text{O}_3 + x\text{CuO}$ ceramics

with $5.0 \leq x \leq 50.0 \text{ mol\%}$ sintered at various temperatures. For the specimens sintered at 875°C , the absolute density increased with increasing CuO content and became saturated when the CuO content exceeded 15.0 mol%. The variation in the absolute density could be explained by that of the microstructure as shown in Fig. 6(a–c). A similar result was also obtained for the specimens sintered at 900°C . For the specimens sintered at 850°C , the density increased with increasing CuO content, but decreased when x exceeded 20.0 mol%. This decrease in density is not completely understood at the present moment. The ϵ_r value significantly increased with the addition of a small amount of CuO and became saturated for the specimens with 15.0 mol% added CuO sintered at 875 and 900°C . In particular, the specimen with a CuO content of 15.0 mol% sintered at 900°C exhibited a high ϵ_r value of 70. In the case of the specimens sintered at 850°C , the ϵ_r value increased with increasing CuO content, but decreased when x exceeded 15.0 mol%. In addition, the variation in the ϵ_r value is the same as that of the density thus, density is an important factor which influences the ϵ_r of the specimen.

Fig. 8 shows the variation in the Q -value of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0 \text{ mol\% B}_2\text{O}_3 + x\text{CuO}$ ceramics with $5.0 \leq x \leq 50.0 \text{ mol\%}$ as a function of the sintering temperature and CuO content. The Q -value increased with increasing sintering temperature, but decreased with increasing CuO content, even though the absolute density increased. This decrease in the Q -value might be related to the increase in the amount of the liquid phase with increasing CuO content. The variation in the τ_f value of

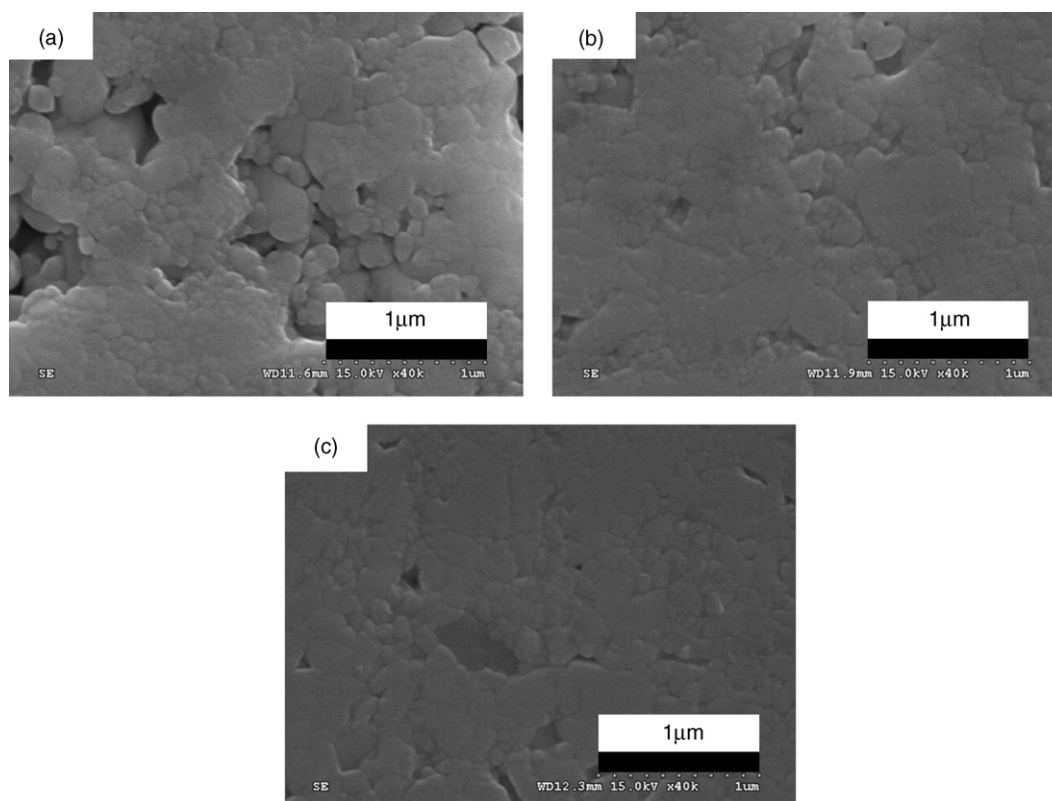


Fig. 6. SEM images of the thermally etched surfaces of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0 \text{ mol\% B}_2\text{O}_3 + x\text{CuO}$ ceramics sintered 875°C for 2 h: (a) $x = 5.0 \text{ mol\%}$, (b) $x = 10.0 \text{ mol\%}$ and (c) $x = 20.0 \text{ mol\%}$.

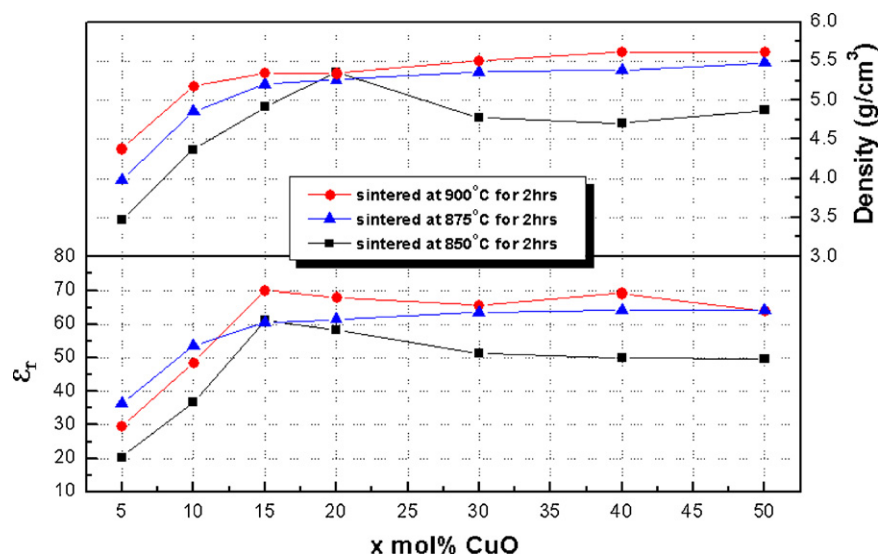


Fig. 7. Variations in the absolute density and ϵ_r value of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0 \text{ mol\% B}_2\text{O}_3 + x\text{CuO}$ ceramics where $5.0 \leq x \leq 50.0 \text{ mol\%}$ sintered at various temperatures.

the specimens sintered at 875°C is also shown in Fig. 8. The τ_f value of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0 \text{ mol\% B}_2\text{O}_3 + 5.0 \text{ mol\% CuO}$ ceramics is about $-11 \text{ ppm}/^\circ\text{C}$ and varied slightly, but non-significantly, with the CuO content. Good microwave dielectric properties of $\epsilon_r = 61.47$, $Q \times f = 4256 \text{ GHz}$ and $\tau_f = -9.25 \text{ ppm}/^\circ\text{C}$, were obtained for the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0 \text{ mol\% B}_2\text{O}_3 + 20.0 \text{ mol\% CuO}$ ceramics sintered at 875°C for 2 h.

To clarify the effect of the $\text{BaCu}(\text{B}_2\text{O}_5)$ phase on the sintering temperature of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics, we made $\text{BaCu}(\text{B}_2\text{O}_5)$ and added it to the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics. When $\text{BaCu}(\text{B}_2\text{O}_5)$ was added, the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics were well sintered even at 875°C . Fig. 9 shows the variations in absolute density, ϵ_r value and Q -value of the $\text{BaCu}(\text{B}_2\text{O}_5)$ added $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics sintered at vari-

ous temperatures for 2 h. The density increased with increasing $\text{BaCu}(\text{B}_2\text{O}_5)$ content and became saturated when 16.0 mol\% of $\text{BaCu}(\text{B}_2\text{O}_5)$ was added. Similar variations were also observed for the ϵ_r value and Q -value. Good dielectric properties of $\epsilon_r = 60.0$ and $Q \times f = 4500 \text{ GHz}$ were obtained for the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramic with 16.0 mol\% of $\text{BaCu}(\text{B}_2\text{O}_5)$ sintered at 875°C . From this result, it can be inferred that $\text{BaCu}(\text{B}_2\text{O}_5)$ second phase was formed in the B_2O_3 and CuO added $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics and helped in the densification at low temperature. Moreover, it can be concluded that the $\text{BaCu}(\text{B}_2\text{O}_5)$ phase is a good additive for decreasing the sintering temperature of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12}$ ceramics without deteriorating the microwave dielectric properties. However, more investigation is required before it can be used in practical applications.

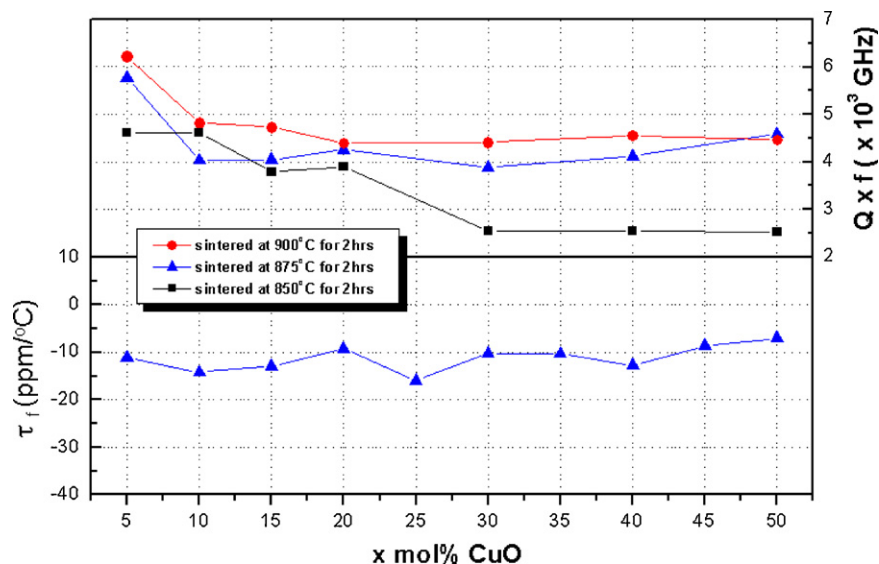


Fig. 8. Variations in the Q -value and τ_f value of the $\text{BaSm}_2\text{Ti}_4\text{O}_{12} + 10.0 \text{ mol\% B}_2\text{O}_3 + x\text{CuO}$ ceramics where $5.0 \leq x \leq 50.0 \text{ mol\%}$ as a function of the sintering temperature and CuO content.

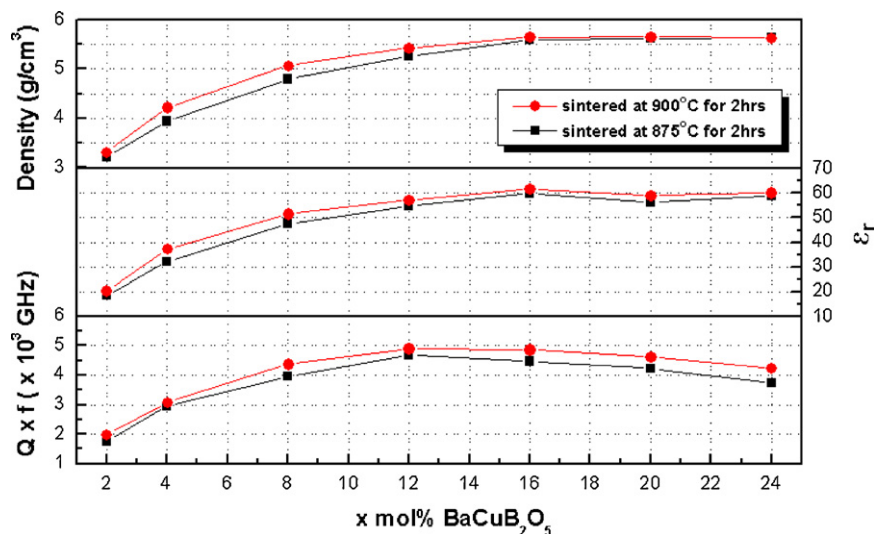


Fig. 9. Variations in the absolute density, ϵ_r value and Q -value of the BaCu(B₂O₅) added BaSm₂Ti₄O₁₂ ceramics sintered at various temperatures for 2 h.

4. Conclusions

The B₂O₃ added BaSm₂Ti₄O₁₂ ceramics were not able to be sintered below 1000 °C. However, when both B₂O₃ and CuO were added, the BaSm₂Ti₄O₁₂ ceramics were sintered even at 850 °C. It is suggested that the BaCu(B₂O₅) phase existed as the liquid phase during the sintering process, and assisted in the densification of the BaSm₂Ti₄O₁₂. However, it is possible that the liquid phase can have the composition other than BaCu(B₂O₅). The ϵ_r value and Q -value increased with the addition of a small amount of CuO. Good microwave dielectric properties of $\epsilon_r = 61.47$, $Q \times f = 4256$ GHz and $\tau_f = -9.25$ ppm/°C were obtained for the BaSm₂Ti₄O₁₂ + 10.0 mol% B₂O₃ + 20.0 mol% CuO ceramics sintered at 875 °C for 2 h.

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